Enabling Room Temperature 2D Dilute Magnetic Semiconductors for Spintronics

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STEVENS

ACADEMICS

DISCOVER STEVENS

RESEARCH

STUDENT LIFE

ADMISSION & AID

Advanced Quantum Materials Lab

The EH Yang group's research aims to translate discoveries in 2D material synthesis into practical applications. The goal is to develop new strategies that combine fundamental studies with forward-looking engineering efforts that would lead to advanced technologies, with implications in fields ranging from quantum sensing and spintronics to energy, environment and medicine.

Advanced Quantum Materials Lab

HOME



MEMS Technologies for Space Applications









Nano Letters, 3(10), 1339 Nanotechnology, 18 IEEE TNANO, 7, 251 IEEE/ASME J MEMS, 15(5), 1214 IEEE/ASME J MEMS, 15(3), 686 IEEE/ASME J MEMS, 15(2), 370 IEEE/ASME J MEMS, 13(5), 799 IEEE/ASME J MEMS, 12(6), 804

STEVENS Advanced Quantum Materials Lab

(2006 – current)

2D Material Synthesis and Nanofabrication



Advanced Materials, 18, 1603898 Nano Letters, 11, 4874 ACS Appl. Mater. Int. **13**(26), 31271



Nature Communications, 11, 2034 Nano Letters, 11(3), 1254 Scientific Reports, (3) 2791



IEEE Sensors Journal, 20(20), 12146 *Annalen der Physik.,* 1800507 *Chemistry of Materials,* 25(19), 3874



Graphene Optoelectronics and Photodetectors



Nano Letters, 11 (3), 1254

Nano Letters, 11, 4874



Scientific Reports, (3) 2571

Scientific Reports, (3), 2791

CNTs for Energy Storage and Sensing PDMS ii) iii) Sheet resistance (Ω/sq) 1000 Transfer Stretch 1st cycle O 30th cycle \Rightarrow \implies □ 50th cycle 800-5th cycle Si/SiO2 substrate Stretched 10th cycle 600-CNT network 400-Individual 0 wavy CNTs 200-0-50 100 Strain(%) c) Nanotechnology 28, 465302, Chemistry of Materials, 25(19), 3874 b) 60 50 40 **₹**30 20 E 10 Stretching -10 Stretch (0% - 160%) -20 Expon. (Stretch) -30 20 µm $1 \, \mu m$ 0.1 0.2 0.3 Voltage (V) 0.4 0.5 30 60 90 120 150 180 Tensile strain (%) 1.2 50 40 8 L. ACS Applied Energy Materials, 2048, 1(5) (1) 20 10 Bending 16 (µA/cm² 0% -10 14 0.7 Bend (0° - 180° 15% -20 40 -Expon. (Bend) 309 0.0 -30 45% 0.1 0.2 0.3 Voltage (V) 0.4 30 60 90 120 150 180 0.5 0 0 20 - 20 -60% Bending angle (°) 75% 150 Pressure sensing 100 6 Response 50 • 0Pa • 500Pa • 509Pa • 975Pa • 1783Pa 10 Glucose sensing Twisting 2 -50 Twist (0° - 180° 0 0 Expon. (Twist) -100 200 300 400 500 600 100 5 10 Stretching Strains (%) 15 0 0.1 0.2 0.3 Voltage (V) 0.3 0.4 90 120 150 180 0 0.5 0 30 60 Time (s) Twist angle (°) IEEE Sensors Journal, 20(20), 12146 IEEE J-Flex, 2(3), 274 Nanotechnology, 30, 095401



TMD Growth and Characterization



Advanced Materials, 18, 1603898, 2D Materials, 4, 025093, Scientific Reports, 10, 1648, Annalen der Physik., 1800507, 2D Materials, 4, 025045, Scientific Reports, 7, 17798, Chemistry of Materials, 30, 5148



Atomically Thin Magnetic Crystals

*in situ d*oping of TMD monolayers enabling 2D dilute magnetic semiconductors

Ferromagnetism with a Curie temperature above room temperature!



Nature Communications, **11**, 2034 (2020), *Scientific Reports*, **12**, 6939 (2022), 2D Materials, **10** 045003 (2023), *Nanotechnology*, **32**. 095708 (2021), ACS Appl. Mater. Interfaces, **13**, 11 (2021)

Discovery of Graphene

- Although scientists knew graphene existed, no-one had worked out how to extract it from graphite.
- That was until it was isolated in 2004 by Geim and Novoselov who received Nobel Prize (2010)







2D Materials beyond Graphene

- Transition metal dichalcogenides (TMDs) can have a *direct bandgap*, complementing graphene.
- TMD monolayers feature strong SOC and inversion symmetry breaking.
- While the conduction band basis is spin degenerate at the K points, the valence band-edge state will split.







Ajayan, Kim, Benerjee, Phys. Today 69, 38, (2016)

Single Crystals of MoS₂ Several Molecular Layers Thick

R. F. FRINDT*

Physics and Chemistry of Solids, Cavendish Laboratory,
CambricCavendish Laboratory,
England(Received 24 March 1965)final form 18 June 1965)

J. Appl. Phys. 37, 1928 (1966); doi: 10.1063/1.1708627

Early workers on electron diffraction prepared thin fragments of $MoS_2^{2,3}$; however no direct thickness measurements were made. It is now well known that small MoS_2 crystals thin enough to be transparent in the electron microscope can be prepared by the stripping technique using adhesive tape. Crystals of

The called scotch tape method for exfoliating graphite

SINGLE-LAYER MoS2

Per Joensen, R.F. Frindt, and S. Roy Morrison Energy Research Institute Department of Physics Simon Fraser University Burnaby, B.C., Cana V5A 1S6

Mat. Res. Bull., Vol. 21, pp. 457-461, 1986. Printed in the USA.

ABSTRACT

 MoS_2 has been exfoliated into monolayers by intercalation with lithium followed by reaction with water. X-ray diffraction analysis has shown that the exfoliated MoS_2 in suspension is in the form of one-moleculethick sheets. X-ray patterns from dried and re-stacked films of exfoliated MoS_2 indicate that the layers are randomly stacked. Exfoliated MoS_2 has been deposited on alumina particles in aqueous suspension, enabling recovery of dry exfoliated MoS_2 supported on alumina.

Exploring exotic properties from exfoliated flakes



Wu, et al., Nature Communications 7, 12955 (2016)



Navarro-Moratalla, et al., Nature Communications 7, 11043 (2016)

A:15 Reflectivity Exciton 1st derivativ of DR/R B:1s A:25 A:18 Free carrier (ii g states ***************** hBN 1L WSe, Upconversion PL A:25 hBN CW Lase Optical SiO, w Gap Si 2.1 2.2 1.7 1.8 1.9 2.0 Energy (eV)

Manca, et al., Nature Communications 8, 14927 (2017)



Novoselov et al., Nature Materials 14, 301 (2015)

Heterostructures Growth via LPCVD



Xu, et al., Nature Materials 13, 1096 (2014)



Ajayan, et al., Nature Materials 13, 1135 (2014)



Duan, et al., Nature Nanotechnology 9, 1024 (2014)

Monolayer Growth via MOCVD and Transfer

MoS₂ on (0001) sapphire



(3x3) MoS₂/(2x2)Al₂O₃



Substrate/Film	a (Å)
(0001)Sapphire	0.476
(0001)SiC	0.307
(0001)GaN	0.319
MoS ₂	0.316
WS ₂	0.316
W/Se	0 332

MoS₂ on (0001) GaN D. Ruzmetov, et al. ACS Nano (2015)





Kis, et al., ACS Nano, 9 (4), 4611 (2015)

😑 Mo

∍ s Al (top) Al (bottom) 0

Park, et al., Nature, 550, 229 (2017)

С

How to cheaply produce large, uniform, highquality layers and heterostructures?



Cheng et al., Nano Lett., 14, 5590 (2014)



Key Challenges Facing TMD Research

- Scaling up (maybe using MOCVD)
- Controlled heterostructure growth
- Control of grain boundaries
 and defects
- Air stability
- Control of doping (alloys)







Najmaei, et al., Nature Materials, 12, 754 (2013)



Park, et al., Nature, 550, 229 (2017)

Control of Stacking Angles

WS_2 on WS_2 (homobilayers)



Scientific Reports, 10, 1648 (2020) *Journal of Physical Chemistry C,* 123(35), 21813 (2019)



Led by Datta (NJIT)



Led by Rahimi-Iman (Philipps-Universität Marburg)



Bilayer

Unpublished

Key Challenges Facing TMD Research

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- Control of grain boundaries
 and defects
- Air stability
- Control of doping (alloys)



Komsa, *et al., PRL*, 109, 035503 (2012)



Najmaei, et al., Nature Materials, 12, 754 (2013)



Park, et al., Nature, 550, 229 (2017)

Air Stability of 2D Materials











Enhanced Air Stability: WS₂ Grown on Graphene



Advanced Materials, 18, 1603898 (2017)

Surface Electric Field and Oxidation



Advanced Materials, 18, 1603898 (2017)

Key Challenges Facing TMD Research

- Scaling up (maybe using MOCVD)
- Controlled heterostructure growth
- Control of grain boundaries
 and defects
- Air stability
- Control of doping (alloys)



Komsa, et al., PRL, 109, 035503 (2012)



Najmaei, et al., Nature Materials, 12, 754 (2013)



Park, et al., Nature, 550, 229 (2017)

Doping of Transition Metal Atoms in TMDs via Chemical Vapor Deposition

- Doping → at the heart of modern semiconductor technologies
- Substitutional doping of 2D TMDs may effectively tune their electrical, optical, magnetic, and catalytic properties.

Ferromagnetism in 2D materials

Re:MoS₂



Zhang et al., Adv. Funct. Mater., 2018, 28, 1706950

Nb:WS₂

Mn:MoS₂



f C A S

Zhang et al., Nano Lett., 2015, **15**, 6586

Gao et al., Adv. Mat., 2016, **28**, 9735

What is Ferromagnetism?

- Intrinsic magnetic dipole moment (on each crystal lattice) align in the same direction.
- Hysteresis
- Curie temperature







B. After magnetization

Ferromagnetism in 2D Limits

- Access the fundamentals of magnetism in reduced dimensions.
- Decouple from the substrates, electrical control, flexible, and functionalized
- Integrate into emergent heterostructures: interplay of distinct physical properties
- Spintronics, quantum information science

- Extrinsic magnetism: defect engineering, surface functionalization, doping
- Intrinsic magnetism: CrX₃ (X = Cl, Br and I), CrGeTe₃, Fe₃GeTe₂, MnX₂ (X = S, Se), VX₂ (X = S, Se, Te), and 2D oxides, halides, nitrides, carbides...



Gong and Zhang, Science, 363(6428), 4450 (2019)

REVIE



RESEAR

Charles

Table 1 | List of p magnetic van der

Research direc-

tions

REVIEW ARTICLE https://doi.org/10.1038/s41565-019-0438-6

Magnetic 2D mate

M. Gibertini^{®1,2}, M. Koperski^{®3,4}, A. I

The family of two-dimensional (2D) materials explored in two dimensions, as well as the possil als currently cover a vast range of properties. Un hongod over the past 2 years with

BUCUSIX, MAGNETISM Waals mate Two-dimensional magnetic crystals Kenneth S. Burch¹, David M and emergent heterostructure device Magnetism, originating from the moving charges and spin of elementary particles, have been and biomedical imposing viagneusin, onginaung nom me moving onarges and spin or elementary paraceter, in revolutionized important technologies such as data storage and biomedical imaging The mean line discontinues to bring forth new phenomena in emergent materials and reduced dimensional (OD) means discussion doe Meals an enclosed and the dimensional (OD) means discussed and the dimensional (OD) and the dimensional (OD) areas Cheng Gong¹ and Xiang Zhang^{1,2*} and communes to bring form new prenomena in emergent materials and reduced uniter The recently discovered two-dimensional (2D) magnetic van der Waals crystals provid ideal ministering for understanding 2D magnetic method and a which has been for The recently discovered two-dimensional (CV) magnetic valuer waas crystals provide ideal platforms for understanding 2D magnetism, the control of which has been full ideal platforms for understanding to vible means to entire and means to entire and means to entire device and the second means to entire and the second means to entire and means to entire device and the second means to entire and the second means to entit to entire and the second means to entire an iveal planorms for atomically thin, flexible magneto-optic and magnetoelectric devi opportunities for atomically thin, flexible magneto-optic and magnetoelectric devi for the commenter existing memories and coin field offect transistory. The commit (such as magnetoresistive memories and spin field-effect transistors). The seamle intervention of 2D means to with discinction cleaters is and whether is and whether is a second whether integration of 2D magnets with dissimilar electronic and photonic materials oper Regration of *LV* magnets with dissimilar electronic and protonic materials oper exciting possibilities for unprecedented properties and functionalities. We review exclume progress in this area and identify the possible directions for device applications, vertex progress in this area and identify the possible directions for device applications, we have the possible directions for device applications. lead to advances in spintronics, sensors, and computing. tion has been used to estimate th peratures of 3D ferromagnets, or centuries, humans had been puzzled argument that the short-range e about the magic attraction of lodestones to action needs to be overcome by iron, and perhaps even more about the fasto randomize the magnetic mor cinating ability of birds, fish, and insects to less, the mean-field picture sui navigate between destinations of thousands tems does not work for the le of miles apart. In early times before the developsystems, in which the dimensio ment of electromagnetism and quantum mechinto play (4). Magnon (i.e., qu to imagine that these intriguing dispersion in 2D systems is re w chare a common magnetic oritally rooted in the

Discovery of Ferromagnetism in 2D Crystals

- In early 2017, the first observations of • ferromagnetism at cryogenic temps were reported.
- Crl_3 on EuS, WSe₂ monolayers on EuS, \bullet WSe₂ monolayers on 10 nm Crl₃.

exfoliated, insulator or conductor, unstable in air





 Crl_3 on EuS $\rightarrow T_c \sim 45K$

Gong, et al., Nature 546, 265 (2017)



WSe₂ on EuS \rightarrow T_c ~ 16.5K

Zhao et al., Nat. Nano., 12, 757 (2017)



 $WSe_2/Crl_3 \rightarrow T_c \sim 61K$

Zhong et al., Sci. Adv., 3, 6586 (2017)

1 JULY 2005 VOL 309 SCIENCE

t *Science*, we tend to get excited about new discoveries that lift the veil a little on how things work, from cells to the universe. That puts our focus firmly on what has been added to our stock of knowledge. For this anniversary issue, we decided to shift our frame of reference, to look instead at what we *don't* know: the scientific puzzles that are driving basic scientific research.

We began by asking *Science*'s Senior Editorial Board, our Board of Reviewing Editors, and our own editors and writers to suggest questions that point to critical knowledge gaps. The ground rules: Scientists should have a good shot at answering the questions over the next 25 years, or they should at least know how to go about answering them. We intended simply to choose 25 of these suggestions and turn them into a survey of the big questions facing science. But when a group of editors and writers sat down to select those big questions, we quickly realized that

25 simply wouldn't convey the grand sweep of cutting-edge research that lies behind the responses we received. So we have ended up with 125 questions, a fitting number for *Science*'s 125th anniversary.

First, a note on what this special issue is not: It is not a survey of the big societal challenges that science can help solve, nor is it a forecast of what science might achieve. Think of it instead as a survey of our scientific ignorance, a broad swath of questions that scientists themselves are asking. As Tom Siegfried puts it in his introductory essay, they are "opportunities to be exploited."

We selected 25 of the 125 questions to highlight based on several criteria: how fundamental they

are, how have few

Is it possible to create magnetic semiconductors that work at room temperature? r scientific disciplines. Some verse, for example. Others we

Such devices have been demonstrated at low temperatures but not yet in a range warm enough for spintronics applications.



Critical Factors for Practical Applications

- Air Stability
- Curie Temperature above RT.....
- Scalability (uniformity).....
- 2D Dilute Magnetic Semiconductors...

2D DMS with High Curie Temperatures?



Ramasubramaniam, Phys Rev. B. 87, 195201 (2013)



5	6	7	8
23	24	25	26
V	Cr	Mn	Fe
41	42	43	
Nb	Мо	Тс	
73	74	75	
Та	W	Re	

Material	Ti	V	Cr	Mn	Fe	Со	Ni
MoS ₂	NM	28 K (Z)	AFM	190 K (Z)	271 K (Z)	AFM	NM
WS ₂	NM	109 K (Z)	AFM	271 K (X-Y)	375 K (X-Y)	AFM	NM
MoSe ₂	NM	224 K (Z)	AFM	131 K (X-Y)	201 K (X-Y)	0 K (Z)	NM
WSe ₂	NM	179 K (Z)	AFM	310 K (X-Y)	331 K (X-Y)	190 K (Z)	NM
MoTe ₂	NM	AFM	AFM	AFM	94 K (Z)	21 K (Z)	NM

Tiwari et al., npj 2D Materials and Applications, 54 (2021)

Antipina et al., Phys. Chem. Chem. Phys., 18, 26956 (2016)

2D DMS with High Curie Temperatures?

6.25% Mn doping 12.5% Mn doping			5	6	7 8	3		
			23 V	24 Cr	25 2 Mn F	6 e		
Fe IS	dop	60	41 Nb	42 Mo	43 Tc			
If Mn of the stitutionally			73 Ta	74 W	75 Re			
Substanto MoS2	Material	Ti	V	Cr	Mn	Fe	Со	Ni
Ramasubra (via CVD)	MoS ₂	NM	28 K (Z)	AFM	190 ł (Z)	(271 K (2)	AFM	NM
	WS ₂	NM	109 К (Z)	AFM	271 k (X-Y)	(375 K (X-Y)	AFM	NM
1.4 - 1.2 - 1.0 -	MoSe ₂	NM	224 K (Z)	AFM	131 H (X-Y)	(X-Y)	0 K (Z)	NM
$Mo_{1-x}Fe_xS_2$	WSe ₂	NM	179 K (Z)	AFM	310 H (X-Y)	K 331 K (X-Y)	190 K (Z)	NM
	MoTe ₂	NM	AFM	AFM	AFM	94 K (Z)	21 K (Z)	NM
Fe concentration Tiwari et al., npi 2D Materials and Applications 54 (2021)								

Antipina et al., Phys. Chem. Chem. Phys., 18, 26956 (2016)

in situ Doping of TMDs via CVD Growth





Gao *et al.*, *Adv. Mat.*, 2016, **28**, 9735-9743 6.7 at% Nb doping of WS₂ monolayer





Zhang *et al., Nano Lett.,* 2015, **15**, 6586-6591 Enhanced 2 at% Mn doping of MoS₂ monolayer via Graphene as a substrate

Ferromagnetism NOT observed

Fe-doping via CVD Growth?



Zhang et al., Nano Lett., 2015, 15, 6586-6591

Gao et al., Adv. Mat., 2016, **28**, 9735-9743

Zhang et al., Adv. Funct. Mater., 2018, 28, 1706950

Contact-Growth of TMDs



Zhang et al., Nano Lett., 2015, 15, 6586-6591

Gao et al., Adv. Mat., 2016, **28**, 9735-9743

Zhang et al., Adv. Funct. Mater., 2018, 28, 1706950

MoS₂ Growth Mechanism

 Initial reaction between MoO₃ and S → intermediate volatile MoO_{3-x}S_y, (for MoS₂) and further sulfurization of MoO_{3-x}S_y → conversion into MoS₂ grains



Cain *et al., ACS Nano* 2016, 10, 5440–5445 Braunecker *et al., Cryst. Growth Des.* 2018, 18, 1012–1019

In situ Fe Doping Process



Shichen Fu Kyungnam Kang



US Patent pending 18/008,126

Nanotechnology, 32. 095708 (2021)

CVD-grown Fe:MoS₂ Monolayers



Nature Communications, 11, 2034 (2020)

CVD-grown Fe:MoS₂ Monolayers





20 µm

Nature Communications, 11, 2034 (2020)

20 µm

Substitutional Doping of Irons











(left, right) Contrast-corrected STEM images of $Fe:WS_2$ and $Fe:MoS_2$ monolayers.

(center) STEM intensity spectra of the selected areas, where Fe atoms exhibit approximately 40% lower intensity than Mo atoms.

Nanotechnology, 32. 095708 (2021)

X-ray Photoelectron Spectroscopy (XPS)



(a) Fe 2*p*3 peaks; (b) Mo 3*d* peaks. The reduced intensity of the Mo-O bond in Fe:MoS₂ (237 eV) as compared to MoS_2 is indicative of an underlying reduction of the sulfur vacancy concentration upon doping; (c) S 2*p* peaks.

Low-Doping Concentration in 2D Materials





V-doped WSe₂

Zhang *et al., Nano Lett.* **15**, 6586-6591 (2015) Gao *et al., Adv. Mater.* **28**, 9735-9743 (2016) Zhang *et al., Adv. Funct. Mater.* **28**, 1706950 (2018)

Yun, et al., Adv. Sci. 1903076 (2020) Duong, et al., Appl. Phys. Lett. **115**, 242406 (2019)

Fe-related PL Emission



Nature Communications, 11, 2034 (2020)

Fe-related Emission from Fe:MoS₂



This Fe-related emission peak is consistent at different excitation wavelengths, showing that this emission is not related to a Raman peak.

Microscopic Origin of the Fe-Related Emission



Unambiguous Fe-related Emission



Meunier group (RPI)

PL spectra of MoS₂ and Fe:MoS₂

DFT calculations of dipole-allowed transitions

Nature Communications, 11, 2034 (2020)

Zeeman Splitting and MCD Effects



- (Right) the conduction band and valence band are split depending on the spin direction (Zeeman splitting).
- This spin-polarized semiconductor band structure alters the absorption of clockwise and counterclockwise-polarized light (MCD effect).



ODMR Spectra of NV⁻ Centers and Superconducting Quantum Interference Device Measurements



Vamivakas group (U. Rochester)

Nature Communications, 11, 2034 (2020)

Fe:MoS₂ vs. Fe:WS₂



Nanotechnology, 32. 095708 (2021)



Fe:WSe₂: Optical, PL & EDS Mapping

Mengqi Fang



unpublished

AFM, STEM, and MFM Measurements



I. Magnetic Proximity Coupling with Fe:MoS₂



Shichen Fu



2D Materials, 10 045003 (2023)

Magneto-optical Characterization of Proximity-coupled Quantum Emitters



X⁰: neutral 2D exciton, X^D: dark 2D exciton transition



II. Spin Photovoltaics with Fe:MoS₂

 A: Fe:MoS₂
 B: Bottom Gr

 B: Bottom Gr
 -65.7 nm

 8.0 μm
 -65.7 nm



Song et al., Sci. Adv. 7, (2021)



Abdus Sarkar

unpublished

III. Magnetic Tunnel Junction

- Electrons flow through the MTJ to transfer spin angular momentum between the magnetic layers.
 - \rightarrow Changing the magnetic state of the free layer, and thus writing information.



Giant tunnelling magnetoresistance at room temperature with MgO (100) tunnel barriers STUART S. P. PARKIN'*, CHRISTIAN KAISER', ALEX PANCHULA', PHILIP M. RICE', BRIAN HUGHES', MAHESH SAMANT' AND SEE-HUN YANG'







Ikeda, Nature Materials, 9.9, 721 (2010)

All 2D Magnetic Tunnel Junction











US Patent pending 18/008,126

Tunneling Characteristics via Fe:MoS₂



Fowler-Nordheim (FN) tunneling

TMR of Fe:MoS₂-based MTJ & Anomalous Hall Effect in Fe₃GeTe₂



Coercivity ~ 0.38T at 30 μA $I_{SD}.$

Aharonov-Bohm Effects in CVD-Graphene Rings

- Aharonov-Bohm (AB) effect: the oscillations in the resistance of a conducting ring as a function of an external magnetic flux piercing the ring.
- An interferometer based on AB oscillations is, in principle, equivalent to a rotation sensor.
- Magnetoconductance show fringes as a function of the applied magnetic field.





Zitao Tang Siwei Chen



Characterization of Aharonov-Bohm Oscillations



FFT of the AB oscillations from a graphene ring

Graphene acts as a 2D ballistic, phase coherent electron system with long phase coherence length -765 nm to 1.25 µm at 4K. (Science, 317(5844), 1530 (2007))

Manuscript in prep.

Summary

 We investigate chemical vapor deposition (CVD)-grown TMDs, including Fe doping of MoS₂, WS₂, WSe₂ and MoSe₂, as well as their heterostructures.



- We demonstrate ferromagnetism in monolayer Fe:MoS₂, demonstrating the magnetic field strength of 0.5 mT at room temperature.
- We currently explore the magnetic proximity coupling of quantum emitters, magnetic tunnel junctions, electron interferometers, and spin photovoltaic devices, which can be readily combined with flexible substrates.
- This research unlocks many new opportunities towards atomically thin magneto-optical and magnetoelectric devices for ultracompact spintronics, on-chip optical communications, and quantum sensing and energy conversion.



Scan me to request 2D magnets for collaboration.